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# **DMMT5551/DMMT5551S**

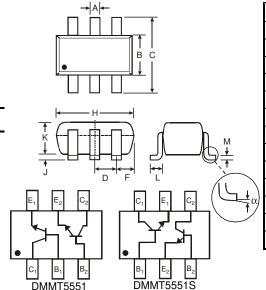
#### MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT)
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

### **Mechanical Data**

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4R & K4T, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



(K4T Marking Code)

	SOT-26										
Dim	Min	Max	Тур								
Α	0.35	0.50	0.38								
В	1.50	1.70	1.60								
С	2.70	3.00	2.80								
D			0.95								
F		_	0.55								
Н	2.90	3.10	3.00								
J	0.013	0.10	0.05								
K	1.00	1.30	1.10								
L	0.35	0.55	0.40								
М	0.10	0.20	0.15								
α	0°	8°	_								
All E	All Dimensions in mm										

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous (Note 2)	Ic	200	mA
Power Dissipation (Note 2, 3)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

DMMT5551

(K4R Marking Code)

#### Notes:

- Built with adjacent die from a single wafer.
- Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation. 3.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

  Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

DS30436 Rev. 8 - 2 DMMT5551/DMMT5551S 1 of 4 © Diodes Incorporated

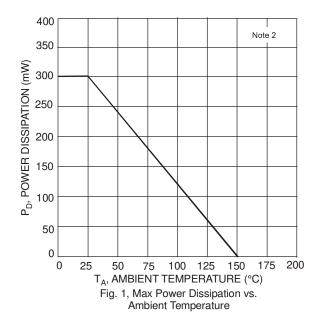


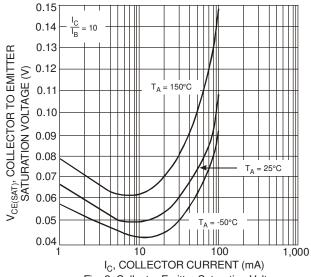
#### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)									
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	180	_	V	$I_C = 100 \mu A, I_E = 0$				
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	160	_	V	$I_C = 1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_E = 10\mu A, I_C = 0$				
Collector Cutoff Current	I <sub>CBO</sub>	_	50	nA μA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0 V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C				
Emitter Cutoff Current	I <sub>EBO</sub>	_	50	nA	$V_{EB} = 4.0 \text{V}, I_C = 0$				
ON CHARACTERISTICS (Note 7)		•	•	•					
DC Current Gain (Note 8)	h <sub>FE</sub>	80 80 30	 250 	_	I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 5.0V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5.0V I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V				
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.15 0.20	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA				
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	1.0	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	C <sub>obo</sub>	_	6.0	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$				
Small Signal Current Gain	h <sub>FE</sub>	50	250	_	$V_{CE} = 10V, I_{C} = 1.0mA,$ f = 1.0kHz				
Current Gain-Bandwidth Product	fT	100	300	MHz	$V_{CE} = 10V, I_{C} = 10mA,$ f = 100MHz				
Noise Figure	NF	_	8.0	dB	$V_{CE} = 5.0V$ , $I_{C} = 200\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$				

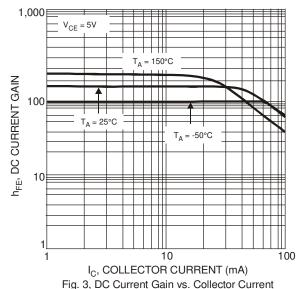
Notes:

- Short duration pulse test used to minimize self-heating effect. The DC Current Gain,  $h_{FE}$ , (matched at  $I_C = 10$ mA and  $V_{CE} = 5$ V) Collector Emitter Saturation Voltage,  $V_{CE(SAT)}$ , and Base Emitter Saturation Voltage,  $V_{BE(SAT)}$  are matched with typical matched tolerances of 1% and maximum of 2%.

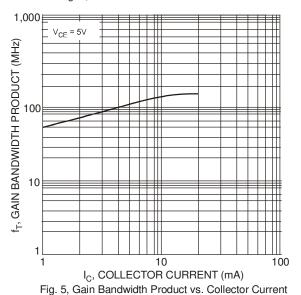








 $V_{CE} = 5V$  $T_A = -50$ °C 8.0 0.2 0.1 10 100 I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 4, Base Emitter Voltage vs. Collector Current

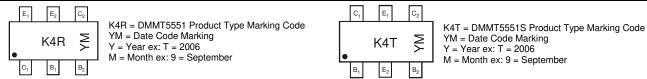


## Ordering Information (Note 6 & 9)

Device	Packaging	Shipping
DMMT5551-7-F	SOT-26	3000/Tape & Reel
DMMT5551S-7-F	SOT-26	3000/Tape & Reel

Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



_ Date Code Key										
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	Т	U	V	W	Χ	Υ	Z

Г	Manala	lan	Fab	Man	A	Mari	livia	led	A	C	0-4	Marr	Dan
	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Ī	Code	1	2	3	4	5	6	7	8	9	0	N	D



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